



Title of Change:	Wafer Fab Transfer for Trench 6 MOSFET Technology to Global Foundries in New York, US.
Proposed Changed Material First Ship Date:	27 Dec 2021 or earlier if approved by customer
Current Material Last Order Date:	27 Jul 2021 <i>Orders received after the Current Material Last Order Date expiration are to be considered as orders for new changed material as described in this PCN. Orders for current (unchanged) material after this date will be per mutual agreement and current material inventory availability.</i>
Current Material Last Delivery Date:	26 Dec 2021 <i>The Current Material Last Delivery Date may be subject to change based on build and depletion of the current (unchanged) material inventory</i>
Product Category:	Active components – Discrete components
Contact information:	Contact your local ON Semiconductor Sales Office or Ammar.Anuar@onsemi.com
PCN Samples Contact:	Contact your local ON Semiconductor Sales Office to place sample order or PCN.samples@onsemi.com Sample requests are to be submitted no later than 45 days after publication of this change notification. Samples delivery timing will be subject to request date, sample quantity and special customer packing/label requirements.
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or Robert.Baran@onsemi.com
Type of Notification:	This is an Initial Product/Process Change Notification (IPCN) sent to customers. An IPCN is an advance notification about an upcoming change and contains general information regarding the change details and devices affected. It also contains the preliminary reliability qualification plan. The completed qualification and characterization data will be included in the Final Product/Process Change Notification (FPCN). This IPCN notification will be followed by a Final Product/Process Change Notification (FPCN) at least 12 months prior to implementation of the change. In case of questions, contact PCN.Support@onsemi.com
Change Category	
Category	Type of Change
Test Flow	Move of all or part of electrical wafer test and/or final test to a different location/site/subcontractor
Process - Wafer Production	Move of all or part of wafer fab to a different location/site/subcontractor New wafer diameter
Equipment	Production from a new equipment/tool which uses the same basic technology (replacement equipment or extension of existing equipment pool) without change of process.
Description and Purpose:	
<p>This Product Change Notification is intended to increase capacity for ON's automotive 30V and 40V Trench 6 MOSFET technology products by transferring wafer fabrication for these products to the Global Foundries Fab located in New York, US.</p> <p>The changes include transferring wafer fabrication, back grind and back metal, to Global Foundries, and utilizing 300mm instead of 200mm diameter wafers. And while the assembly location remains unchanged (at ON Semiconductor, Seremban, Malaysia), wafer saw and die attach tooling are being updated to accommodate 300mm wafers.</p>	



There is no change to the orderable part number.

There is no product marking change as a result of this change.

	Before Change	After Change
Wafer Fabrication Site	ON Aizu, Japan ON Gresham, US	<u>Global Foundries, US</u>
Wafer Diameter	200mm (existing sites)	300mm (Global Foundries)
Wafer Probe Site	ON Seremban, Malaysia	<u>Global Foundries, US</u>
Back Grind, Back Metal Site	ON ISMF, Malaysia	<u>Global Foundries, US</u>

Reason / Motivation for Change:	Source/Supply/Capacity Changes Process/Materials Change
Anticipated impact on fit, form, function, reliability, product safety or manufacturability:	The device has been qualified and validated based on the same Product Specification. The device has successfully passed the qualification tests. Potential impacts can be identified, but due to testing performed by ON Semiconductor in relation to the PCN, associated risks are verified and excluded. No anticipated impacts.

Sites Affected:	
ON Semiconductor Sites	External Foundry/Subcon Sites
On Semiconductor Gresham, United States	GlobalFoundries, Fab 10, New York, US
ON Semiconductor Aizu, Japan	
ON Semiconductor Seremban, Malaysia	

Marking of Parts/ Traceability of Change:	Material will be traceable with ONs lot trace code & tracking
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Reliability Data Summary:

(QV4) NVMF55C404NLT1G
RMS: 66099 & 67566
PACKAGE: SO8FL-HE

Test	Specification	Condition	Interval
HTRB	JESD22-A108	Ta=150°C, 100% max rated Vds	2016 hrs
HTGB	JESD22-A108	Ta= -150°C, 100% max rated Vgss	2016 hrs
HTSL	JESD22-A103	Ta= 150°C	2016 hrs
IOL	MIL-STD-750 (M1037) AEC-Q101	Ta=+25°C, delta Tj=100°C On/off =2 min	30000 cyc
TC	JESD22-A104	Ta= -55°C to +150°C	1000 cyc
HAST	JESD22-A110	130°C, 85% RH, 18.8psig, bias	192 hrs
uHAST	JESD22-A118	130°C, 85% RH, 18.8psig, unbiased	96 hrs
PC	J-STD-020 JESD-A113	MSL1 @ 260°C	
RSH	JESD22- B106	Ta = 265C, 10 sec	

**(QV5) NVTF55C680NLTAG**

RMS: 66103

PACKAGE: u8FL

Test	Specification	Condition	Interval
TC	JESD22-A104	Ta= -55°C to +150°C	1000 cyc
HAST	JESD22-A110	130°C, 85% RH, 18.8psig, bias	192 hrs
uHAST	JESD22-A118	130°C, 85% RH, 18.8psig, unbiased	96 hrs
PC	J-STD-020 JESD-A113	MSL1 @ 260°C	

(QV6) NVMF55C404NWFT3G-K

RMS: 66100

PACKAGE: SO8FL-HE

Test	Specification	Condition	Interval
HTGB	JESD22-A108	Ta= -150°C, 100% max rated Vgss	2016 hrs

Estimated date for qualification completion: 27 November 2020

Electrical Characteristics Summary:

Electrical characteristics are not impacted.

List of Affected Parts:

Note: Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the [PCN Customized Portal](#).

Current Part Number	New Part Number	Qualification Vehicle
NVMF55C404NAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C404NLAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C410NLAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C410NT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C423NLAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C423NLT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C426NT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C430NAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C430NLAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C430NLT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C430NT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C442NAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K



Initial Product/Process Change Notification
 Document #: IPCN22966ZC
 Issue Date: 21 Aug 2020

NVMF55C442NT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C450NAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C450NLAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C450NLAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C450NLT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C450NLT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C450NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C450NT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C456NLAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C456NLAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C456NLT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C456NLT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C456NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C460NLAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C460NLAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C460NLT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C460NLT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C460NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVTF55C453NLTAG	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K, NVTF55C680NLTAG
NVTF55C466NLTAG	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K, NVTF55C680NLTAG
NVMF54C03NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF54C03NT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF54C05NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF54C05NT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF54C302NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVTF54C05NTAG	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K, NVTF55C680NLTAG
NVTF54C13NTAG	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K, NVTF55C680NLTAG
NVTF54C13NTWG	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K, NVTF55C680NLTAG
NVMF54C01NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF54C01NT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C404NAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C404NLAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C404NLT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K



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NVMF55C404NLT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C404NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C404NT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C410NAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C410NAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C410NLAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C410NLT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C410NLT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C410NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C423NLAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C423NLT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C426NAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C426NAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C426NLT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C426NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C430NAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C430NLAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C430NLT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C430NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C442NAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C442NLAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C442NLAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C442NLT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C442NLT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C442NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C450NAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K

Japanese translation of the notification starts here.
通知の日本語訳はここから始まります。

Note: The Japanese version is for reference only. In case of any differences between the English and Japanese version, the English version shall control.

注：日本語版は参照用です。英語版と日本語版の違いがある場合は、英語版が優先されます。



初回製品 / プロセス変更通知

文書番号# : IPCN22966ZC

発行日 : 21 Aug 2020

変更件名:	グローバルファンドリー(ニューヨーク、米国)にて Trench 6 MOSFET テクノロジー製品のウェハー工場生産能力拡大
初回出荷予定日:	27 Dec 2021 またはお客様からの承認が得られた場合はそれ以前.
現在の材料の最終注文日:	27 Jul 2021 既存品の最終注文日以降の注文は、この PCN に記載されている変更後品の注文とみなされます。この日付より後の既存品(変更前品)の注文は、相互契約により変更前品の在庫状況に応じて履行されます。
現在の材料の最終出荷日:	26 Dec 2021 既存品(変更前品)の最終出荷日は、変更前品の製造および在庫の状況によって変更されることがあります。
製品カテゴリ:	アクティブなコンポーネント - 個別コンポーネント
連絡先情報:	現地のオン・セミコンダクター営業所または Ammar.Anuar@onsemi.com にお問い合わせください。
サンプル:	現地のオン・セミコンダクター営業所に注文するか、また PCN.samples@onsemi.com にお問い合わせください。 サンプルは、この変更通知の発行から 45 日以内に要求してください。 サンプル納入時は、依頼日、数量、特別梱包材/ラベル条件によって異なります。
追加の信頼性データ:	お客さまの地域のオン・セミコンダクター営業所または Robert.Baran@onsemi.com にお問い合わせください。
通知種別:	これは、お客様宛の初回製品 / プロセス変更通知 (IPCN) です。IPCN は、近日中に実施される変更に関する事前通知であり、変更の詳細および影響を受けるデバイスについての一般情報が記載されます。また、暫定的な信頼性認証計画も記載されます。 最終的な認定データおよび特性データは最終製品 / プロセス変更通知 (FPCN) に含まれます。この IPCN は、変更実施から少なくとも 12 か月前に発行される最終製品 / プロセス変更通知 (FPCN) に先だって通知されます。ご不明な点がありましたら PCN.Support@onsemi.com にお問い合わせください。
変更カテゴリ:	変更種別
テストフロー	電氣的ウェハテストのすべて、一部または最終テスト(あるいはその両方)を異なる場所 / 拠点 / 外注へ移管
プロセス - ウェハー製造	ウェハ工程のすべてまたは一部の異なる場所 / 拠点 / 半導体サブコンへの移動 新規ウェハー径
装置	プロセス変更をとまなわない同じ基本技術を使用した新しい装置 / ツール(装置の交換または既存装置の増設)での生産。

説明および目的:

この製品変更通知は、ON の自動車用 30V および 40V トレンチ 6 MOSFET テクノロジー製品のウェハー製造を、米国ニューヨーク州にある Global Foundries Fab に移すことにより、これらの製品の容量を増やすことを目的としています。

変更には、ウェハー製造、バックグランドおよびバックメタルのグローバルファウンドリーへの転送、および直径 200mm ではなく 300mm ウェハーの利用が含まれます。また、アセンブリの場所は変更されていませんが(オンセミコンダクター、マレーシアのスレンバン)、300mm ウェハーに対応するようにウェハーソーとダイアタッチツールが更新されています。

オーダー可能な製品番号に変更はありません。

本変更の結果として製品マーキングに変更はありません。

	Before Change	After Change
ウェハー製造拠点	ON Aizu, Japan ON Gresham, US	Global Foundries, US
ウェハー径	200mm (existing sites)	300mm (Global Foundries)
ウェハープローブ拠点	ON Seremban, Malaysia	Global Foundries, US
バックグランド、バックメタル拠点	ON ISMF, Malaysia	Global Foundries, US



変更の理由 / 動機:	ソース/供給/容量変更プロセス/材料変更		
適合性、形状、機能、信頼性、製品安全性、または製造可能性に関して見込まれる影響	<p>デバイスは同じ製品仕様に基づいて認定および検証されています。デバイスは認定試験に正常に合格しています。潜在的な影響が確認される可能性があります。オン・セミコンダクターが PCN に関して実施する検査により、関連するリスクは検証および排除されます。</p> <p>予想される影響はありません。</p>		
影響を受ける拠点:			
オン・セミコンダクター拠点:	外部製造工場 / 下請業者拠点:		
On Semiconductor Gresham, United States	GlobalFoundries, Fab 10, New York, US		
ON Semiconductor Aizu, Japan			
ON Semiconductor Seremban, Malaysia			
部品の表示 / 変更の追跡可能性:	材料はオンのトレースコードとトラッキングにてトレースできます。		
信頼性データの要約:			
(QV4) NVMF55C404NLT1G			
RMS: 66099 & 67566			
パッケージ: SO8FL-HE			
Test	Specification	Condition	Interval
HTRB	JESD22-A108	Ta=150°C, 100% max rated Vds	2016 hrs
HTGB	JESD22-A108	Ta= 150°C, 100% max rated Vgss	2016 hrs
HTSL	JESD22-A103	Ta= 150°C	2016 hrs
IOL	MIL-STD-750 (M1037) AEC-Q101	Ta=+25°C, delta Tj=100°C On/off =2 min	30000 cyc
TC	JESD22-A104	Ta= -55°C to +150°C	1000 cyc
HAST	JESD22-A110	130°C, 85% RH, 18.8psig, bias	192 hrs
uHAST	JESD22-A118	130°C, 85% RH, 18.8psig, unbiased	96 hrs
PC	J-STD-020 JESD-A113	MSL1 @ 260°C	
RSH	JESD22- B106	Ta = 265C, 10 sec	
(QV5) : NVTFS5C680NLTAG			
RMS : 66103			
パッケージ: u8FL			
Test	Specification	Condition	Interval
TC	JESD22-A104	Ta= -55°C to +150°C	1000 cyc
HAST	JESD22-A110	130°C, 85% RH, 18.8psig, bias	192 hrs
uHAST	JESD22-A118	130°C, 85% RH, 18.8psig, unbiased	96 hrs
PC	J-STD-020 JESD-A113	MSL1 @ 260°C	
(QV6) : NVMF55C404NWFT3G-K			
RMS : 66100			
パッケージ: SO8FL-HE			
Test	Specification	Condition	Interval
HTGB	JESD22-A108	Ta= 150°C, 100% max rated Vgss	2016 hrs
認定完了予定日: 27 November 2020			



電气的特性の要約:

電气的特性への影響はありません。

影響を受ける部品の一覧:

注: 標準の部品番号(既製品)のみが部品一覧に記載されます。本 PCN に影響を受けるカスタム 部品は、PCN メールのお客様の特定の PCN の付属文書、または PCN カスタマイズポータルに記載されています。

現在の部品番号	新部品番号	認定試験用ピークル
NVMF55C404NAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C404NLAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C410NLAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C410NT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C423NLAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C423NLT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C426NT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C430NAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C430NLAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C430NLT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C430NT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C442NAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C442NT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C450NAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C450NLAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C450NLAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C450NLT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K



NVMF55C450NLT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C450NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C450NT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C456NLAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C456NLAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C456NLT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C456NLT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C456NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C460NLAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C460NLAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C460NLT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C460NLT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C460NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVTF55C453NLTAG	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K, NVTF55C680NLTAG
NVTF55C466NLTAG	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K, NVTF55C680NLTAG
NVMF54C03NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF54C03NT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF54C05NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF54C05NT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF54C302NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVTF54C05NTAG	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K, NVTF55C680NLTAG



NVTFS4C13NTAG	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K, NVTFS5C680NLTAG
NVTFS4C13NTWG	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K, NVTFS5C680NLTAG
NVMF54C01NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF54C01NT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C404NAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C404NLAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C404NLT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C404NLT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C404NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C404NT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C410NAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C410NAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C410NLAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C410NLT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C410NLT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C410NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C423NLAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C423NLT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C426NAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C426NAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C426NLT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K



NVMF55C426NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C430NAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C430NLAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C430NLT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C430NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C442NAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C442NLAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C442NLAFT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C442NLT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C442NLT3G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C442NT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K
NVMF55C450NAFT1G	NA	NVMF55C404NLT1G, NVMF55C404NWFT3G-K